

## Silicon NPN Power Transistors

2SC1185

## DESCRIPTION

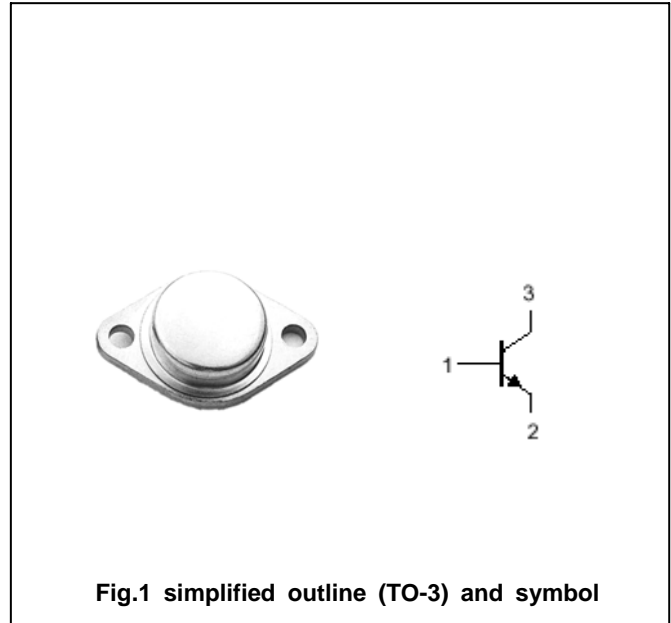
- With TO-3 package
- Wide area of safe operation
- High breakdown voltage  
:  $V_{CEO}=250V(\text{min})$

## APPLICATIONS

- For voltage regulator, inverter, switching mode power supply applications.

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a=^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	250	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		0.7	A
$P_D$	Total power dissipation	$T_C=25^{\circ}\text{C}$	50	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA; I <sub>B</sub> =0	250			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =500mA; I <sub>B</sub> =100mA			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =500mA; I <sub>B</sub> =100mA			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V	40		200	

PACKAGE OUTLINE

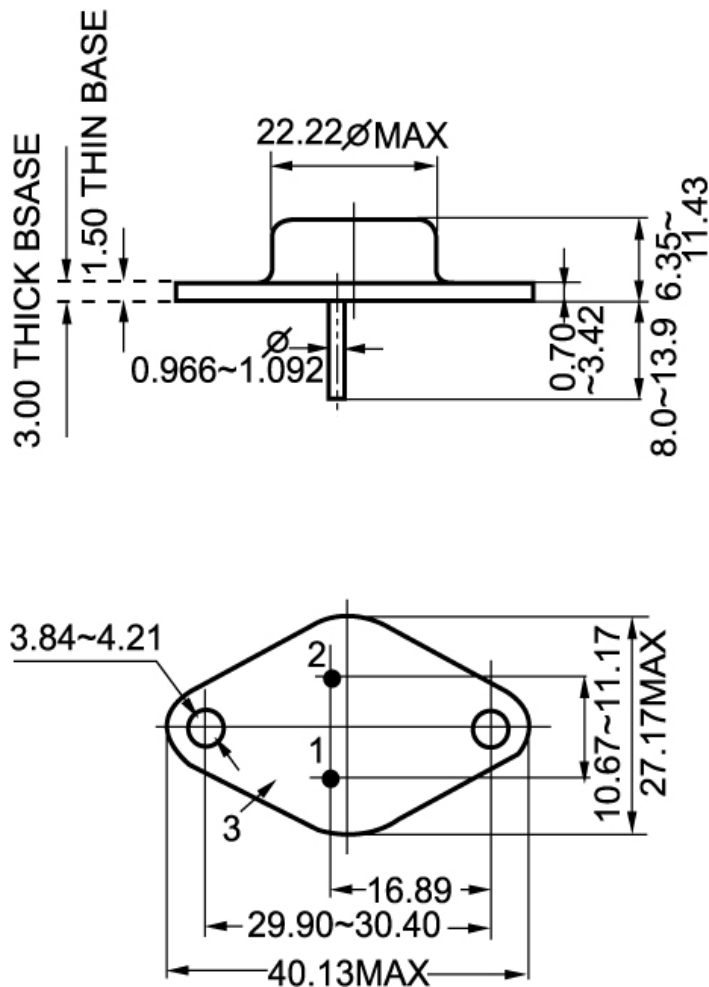


Fig.2 outline dimensions